

## **INCHANGE SEMICONDUCTOR**

## **isc** Silicon NPN Darlington Power Transistor

# 2SD1589

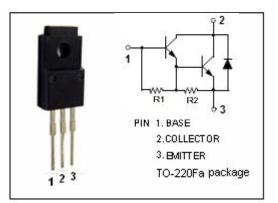
### DESCRIPTION

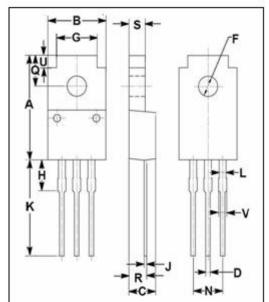
- Collector-Emitter Saturation Voltage-
  - : V<sub>CE(sat)</sub>= 1.5V(Max) @I<sub>C</sub>= 2A
- High DC Current Gain

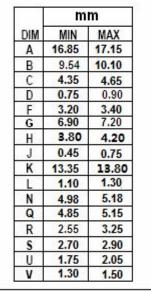
   hFE= 2000(Min) @ I<sub>C</sub>= 2A
- Complement to Type 2SB1098
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

• Designed for audio frequency power amplifier and low speed switching industrial use.







## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	100	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
lc	Collector Current-Continuous	5	А	
Іср	Collector Current-Pulse	10	А	
I <sub>B</sub>	Base Current-Continuous	0.5	А	
Pc	Collector Power Dissipation @ T₂=25℃	2	W	
	Collector Power Dissipation @ T <sub>c</sub> =25°C	20		
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	

isc website: <u>www.iscsemi.com</u>



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### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!^{\circ}\!\!^{\circ}\!\!^{\circ}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 2mA			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 2mA			2.0	V
I <sub>СВО</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0			1.0	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>ЕВ</sub> = 5V; I <sub>C</sub> = 0			3.0	mA
h <sub>FE -1</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 2V	2000		20000	
h <sub>FE -2</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 2V	500			

#### Switching times

t <sub>on</sub>	Turn-on Time		1.0	μ <b>S</b>
t <sub>stg</sub>	Storage Time	$I_{C}$ = 2A, $I_{B1}$ = $I_{B2}$ = 2mA; R <sub>L</sub> = 25 $\Omega$ ; V <sub>CC</sub> $\approx$ 50V	3.5	μ <b>S</b>
t <sub>f</sub>	Fall Time		1.2	μS

#### • h<sub>FE-1</sub> Classifications

М	Ļ	к
2000-5000	4000-10000	8000-20000

### **NOTICE:**

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